

FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 05-720-US2	Serial No. 10/559,981
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant: Kouvetakis, et al.	
		Filing Date: December 8, 2005	Group: 2812

RSP	70.	R. Gaska, A. Zukauskas, M. S. Shur, and M. A. Khan, "Progress in III-nitride based white light sources", <i>Proceedings of the SPIE</i> , Vol: 4776, pp. 82-96 (2002).
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EXAMINER 	DATE CONSIDERED 4/19/07
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